



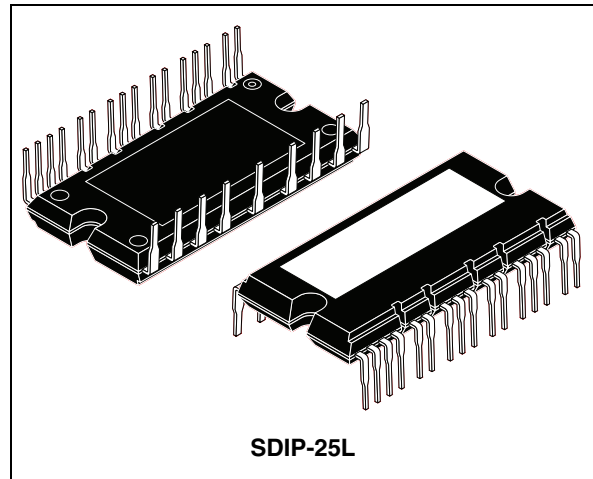
STGIPS30C60

SLLIMM™ small low-loss intelligent molded module
IPM, 3-phase inverter - 30 A, 600 V short-circuit rugged IGBT

Target specification

Features

- IPM 30 A, 600 V 3-phase IGBT inverter bridge including control ICs for gate driving and free-wheeling diodes
- Short-circuit rugged IGBTs
- 3.3 V, 5 V, 15 V CMOS/TTL inputs comparators with hysteresis and pull down / pull up resistors
- Undervoltage lockout
- Internal bootstrap diode
- Interlocking function
- Smart shutdown function
- Comparator for fault protection against over temperature and overcurrent
- DBC leading to low thermal resistance
- Isolation rating of 2500 V_{rms}/min



Applications

- 3-phase inverters for motor drives
- Air conditioners

Description

This intelligent power module provides a compact, high performance AC motor drive in a simple, rugged design. Combining ST proprietary control ICs with the most advanced short-circuit-rugged IGBT system technology, this device is ideal for 3-phase inverters in applications such as motor drives and air conditioners. SLLIMM™ is a trademark of STMicroelectronics.

Table 1. Device summary

Order code	Marking	Package	Packaging
STGIPS30C60	GIPS30C60	SDIP-25L	Tube

Contents

- 1 Internal block diagram and pin configuration 3**
- 2 Electrical ratings 5**
 - 2.1 Absolute maximum ratings 5
 - 2.2 Thermal data 6
- 3 Electrical characteristics 7**
 - 3.1 Control part 9
 - 3.2 Waveforms definitions 11
- 4 Smart shutdown function 12**
- 5 Applications information 14**
 - 5.1 Recommendations 15
- 6 Package mechanical data 16**
- 7 Revision history 19**

1 Internal block diagram and pin configuration

Figure 1. Internal block diagram

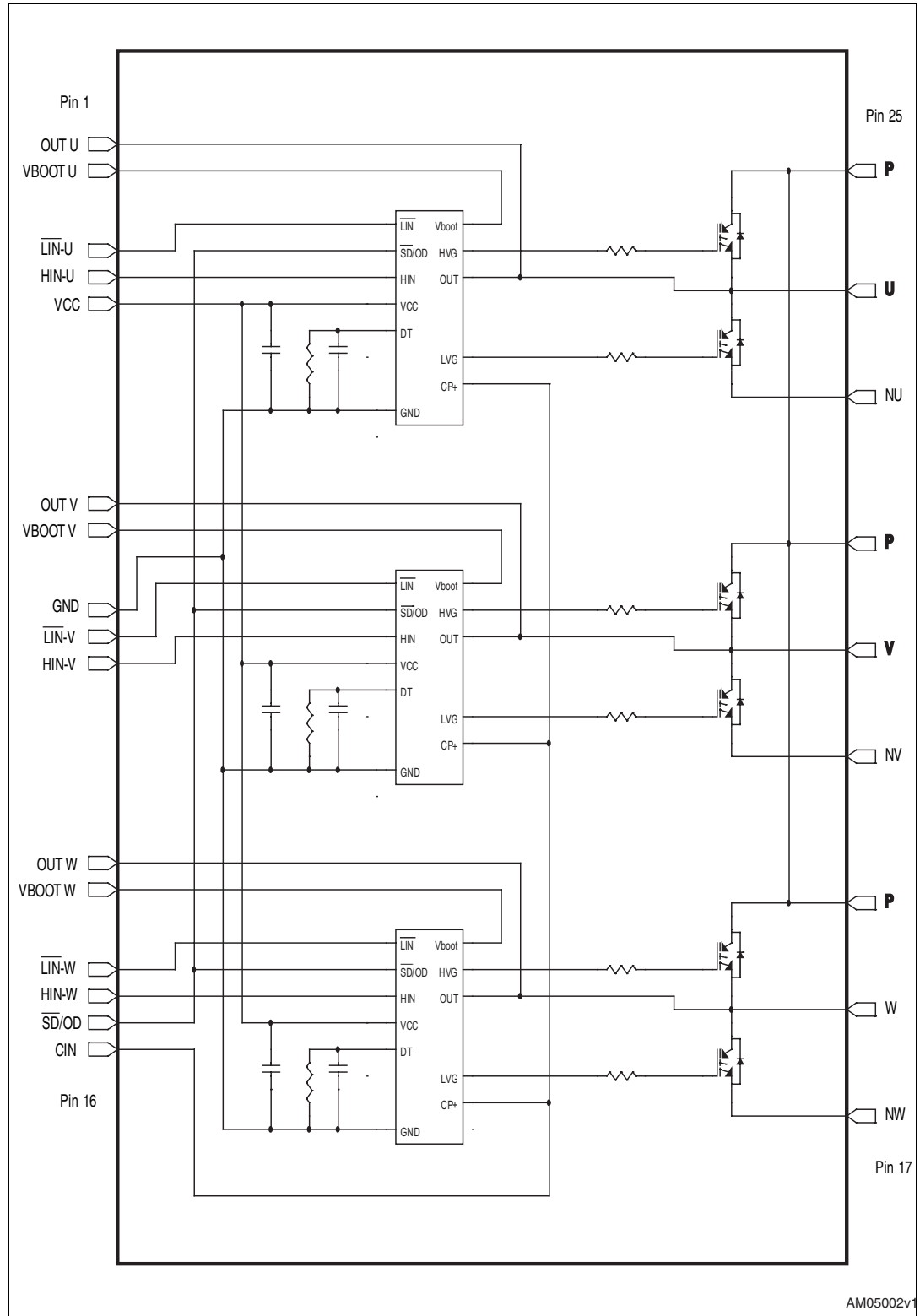
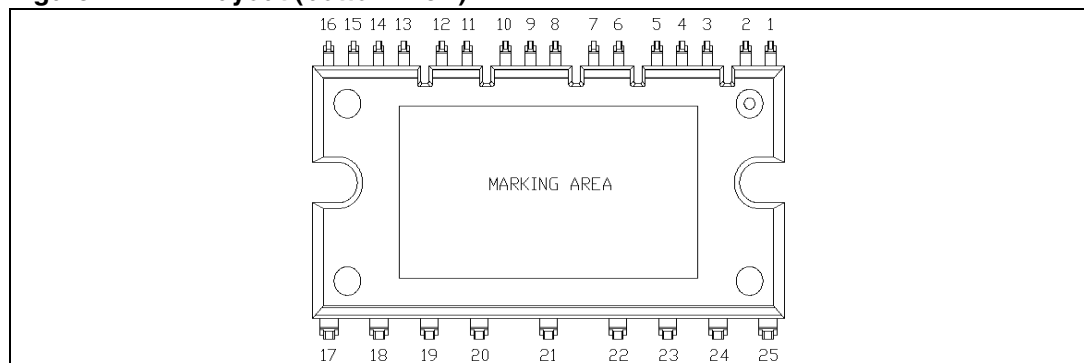


Table 2. Pin description

Pin n°	Symbol	Description
1	OUT _U	High-side reference output for U phase
2	V _{bootU}	Bootstrap voltage for U phase
3	$\overline{\text{LIN}}_{\text{U}}$	Low-side logic input for U phase
4	HIN _U	High-side logic input for U phase
5	V _{CC}	Low voltage power supply
6	OUT _V	High-side reference output for V phase
7	V _{boot V}	Bootstrap voltage for V phase
8	GND	Ground
9	$\overline{\text{LIN}}_{\text{V}}$	Low-side logic input for V phase
10	HIN _V	High-side logic input for V phase
11	OUT _W	High-side reference output for W phase
12	V _{boot W}	Bootstrap voltage for W phase
13	$\overline{\text{LIN}}_{\text{W}}$	Low-side logic input for W phase
14	HIN _W	High-side logic input for W phase
15	$\overline{\text{SD}} / \text{OD}$	Shutdown logic input (active low) / open-drain (comparator output)
16	CIN	Comparator input
17	N _W	Negative DC input for W phase
18	W	W phase output
19	P	Positive DC input
20	N _V	Negative DC input for V phase
21	V	V phase output
22	P	Positive DC input
23	N _U	Negative DC input for U phase
24	U	U phase output
25	P	Positive DC input

Figure 2. Pin layout (bottom view)



2 Electrical ratings

2.1 Absolute maximum ratings

Table 3. Inverter part

Symbol	Parameter	Value	Unit
V_{PN}	Supply voltage applied between P - N _U , N _V , N _W	450	V
$V_{PN(surge)}$	Supply voltage (surge) applied between P - N _U , N _V , N _W	500	V
V_{CES}	Each IGBT collector emitter voltage ($V_{IN}^{(1)} = 0$)	600	V
$\pm I_C^{(2)}$	Each IGBT continuous collector current at $T_C = 25^\circ\text{C}$	30	A
$\pm I_{CP}^{(3)}$	Each IGBT pulsed collector current	100	A
P_{TOT}	Each IGBT total dissipation at $T_C = 25^\circ\text{C}$	TBD	W
t_{scw}	Short circuit withstand time, $V_{CE} = 0.5 V_{(BR)CES}$ $T_J = 125^\circ\text{C}$, $V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN}^{(1)} = 0 \div 5\text{ V}$	5	μs

1. Applied between HIN_i, $\overline{\text{LIN}}_i$ and GND for $i = U, V, W$
2. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

3. Pulse width limited by max junction temperature

Table 4. Control part

Symbol	Parameter	Value	Unit
V_{OUT}	Output voltage applied between OUT _U , OUT _V , OUT _W - GND	$V_{boot} - 21$ to $V_{boot} + 0.3$	V
V_{CC}	Low voltage power supply	-0.3 to +21	V
V_{CIN}	Comparator input voltage	-0.3 to $V_{CC} + 0.3$	V
V_{boot}	Bootstrap voltage applied between $V_{boot\ i} - \text{OUT}_i$ for $i = U, V, W$	-0.3 to 620	V
V_{IN}	Logic input voltage applied between HIN, $\overline{\text{LIN}}$ and GND	-0.3 to 15	V
$V_{SD/OD}$	Open drain voltage	-0.3 to 15	V
dV_{OUT}/dt	Allowed output slew rate	50	V/ns

Table 5. Total system

Symbol	Parameter	Value	Unit
V_{ISO}	Isolation withstand voltage applied between each pin and heatsink plate (AC voltage, $t = 60$ sec.)	2500	V
$T_j^{(1)}$	Operating junction temperature	-40 to 150	°C
T_C	Module case operation temperature	-40 to 125	°C

1. The maximum junction temperature rating of the power chips integrated within the SDIP module is 150°C (@ $T_C \leq 100^\circ\text{C}$). To ensure safe operation of the SDIP module, the average junction temperature should be limited to $T_{j(\text{avg})} \leq 125^\circ\text{C}$ (@ $T_C \leq 100^\circ\text{C}$)

2.2 Thermal data

Table 6. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case single IGBT	TBD	°C/W
	Thermal resistance junction-case single diode	TBD	°C/W

3 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

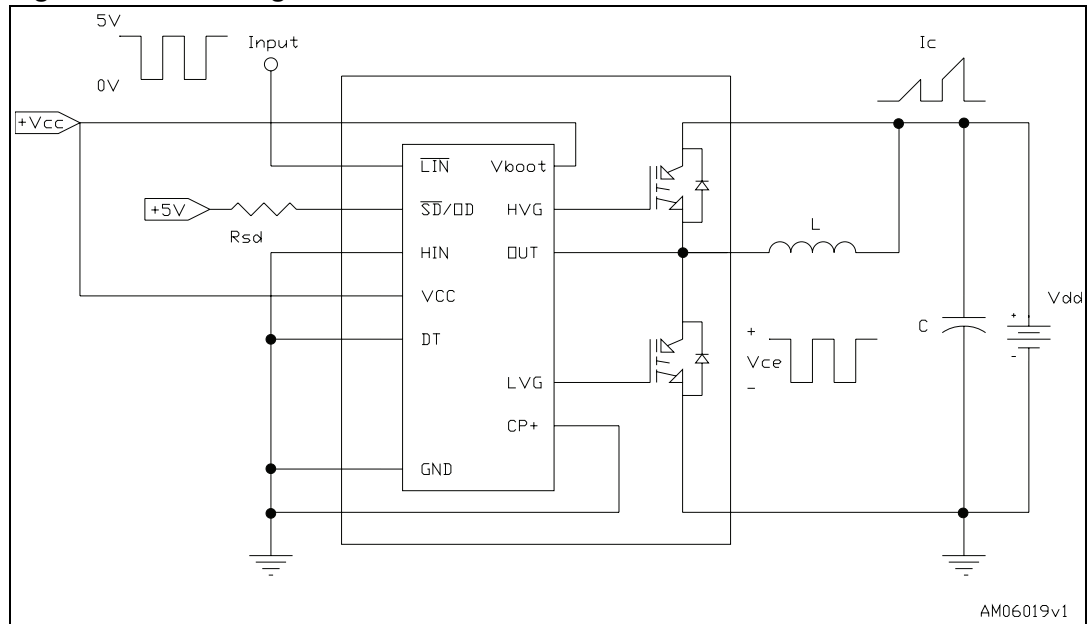
Table 7. Inverter part

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN}^{(1)} = 0 \div 5\text{ V}$, $I_C = 30\text{ A}$	-	1.9		V
		$V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN}^{(1)} = 0 \div 5\text{ V}$, $I_C = 30\text{ A}$, $T_J = 125\text{ °C}$	-	2.0		
I_{CES}	Collector-cut off current ($V_{IN}^{(1)} = 0$ "logic state")	$V_{CE} = 600\text{ V}$, $V_{CC} = V_{Boot} = 15\text{ V}$	-		TBD	μA
V_F	Diode forward voltage	$V_{IN}^{(1)} = 0$ "logic state", $I_C = 30\text{ A}$	-		2.2	V
Inductive load switching time and energy						
t_{on}	Turn-on time	$V_{PN} = 300\text{ V}$, $V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN}^{(1)} = 0 \div 5\text{ V}$, $I_C = 30\text{ A}$ (see Figure 3)	-	TBD	-	ns
$t_{c(on)}$	Crossover time (on)		-	TBD	-	
t_{off}	Turn-off time		-	TBD	-	
$t_{c(off)}$	Crossover time (off)		-	TBD	-	
t_{rr}	Reverse recovery time		-	TBD	-	μJ
E_{on}	Turn-on switching losses		-	TBD	-	
E_{off}	Turn-off switching losses		-	TBD	-	

1. Applied between HIN_i , \overline{LIN}_i and GND for $i = U, V, W$. (\overline{LIN} inputs are active-low).

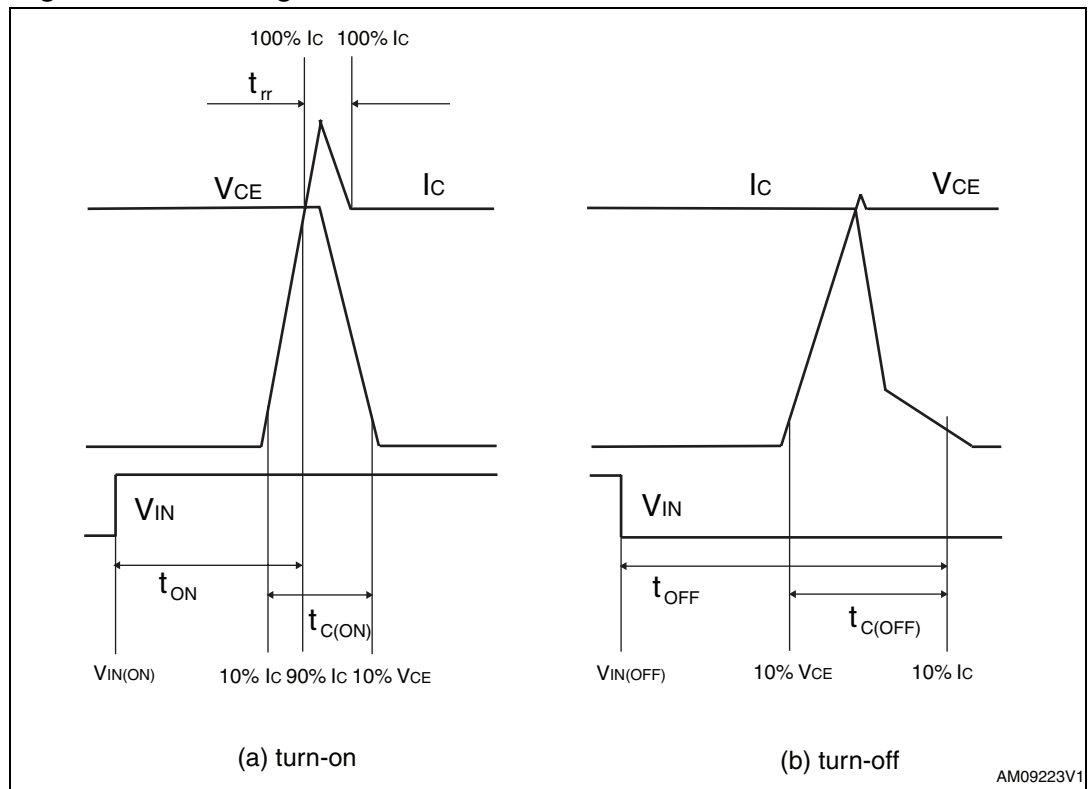
Note: t_{ON} and t_{OFF} include the propagation delay time of the internal drive. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the internally given gate driving condition.

Figure 3. Switching time test circuit



AM06019v1

Figure 4. Switching time definition



AM09223V1

Figure 4 "Switching time definition" refers to HIN inputs (active high). For LIN inputs (active low), VIN polarity must be inverted for turn-on and turn-off.

3.1 Control part

Table 8. Low voltage power supply ($V_{CC} = 15\text{ V}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC_hys}	V_{CC} UV hysteresis		1.2	1.5	1.8	V
V_{CC_thON}	V_{CC} UV turn ON threshold		11.5	12	12.5	V
V_{CC_thOFF}	V_{CC} UV turn OFF threshold		10	10.5	11	V
I_{qccu}	Undervoltage quiescent supply current	$V_{CC} = 10\text{ V}$ $\overline{SD}/OD = 5\text{ V}$; $\overline{LIN} = 5\text{ V}$; $HIN = 0$, $CIN = 0$			450	μA
I_{qcc}	Quiescent current	$V_{CC} = 15\text{ V}$ $\overline{SD}/OD = 5\text{ V}$; $\overline{LIN} = 5\text{ V}$ $HIN = 0$, $CIN = 0$			3.5	mA
V_{ref}	Internal comparator (CIN) reference voltage		0.5	0.54	0.58	V

Table 9. Bootstrapped voltage ($V_{CC} = 15\text{ V}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{BS_hys}	V_{BS} UV hysteresis		1.2	1.5	1.8	V
V_{BS_thON}	V_{BS} UV turn ON threshold		10.6	11.5	12.4	V
V_{BS_thOFF}	V_{BS} UV turn OFF threshold		9.1	10	10.9	V
I_{QBSU}	Undervoltage V_{BS} quiescent current	$V_{BS} = 10\text{ V}$ $\overline{SD}/OD = 5\text{ V}$; \overline{LIN} and $HIN = 5\text{ V}$; $CIN = 0$		70	110	μA
I_{QBS}	V_{BS} quiescent current	$V_{BS} = 15\text{ V}$ $\overline{SD}/OD = 5\text{ V}$; \overline{LIN} and $HIN = 5\text{ V}$; $CIN = 0$		150	210	μA
$R_{DS(on)}$	Bootstrap driver on resistance	LVG ON		120		Ω

Table 10. Logic inputs ($V_{CC} = 15\text{ V}$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{il}	Low logic level voltage				0.8	V
V_{ih}	High logic level voltage		2.25			V
I_{HINh}	HIN logic "1" input bias current	$HIN = 15\text{ V}$	110	175	260	μA
I_{HINl}	HIN logic "0" input bias current	$HIN = 0\text{ V}$			1	μA
I_{LINl}	\overline{LIN} logic "1" input bias current	$\overline{LIN} = 0\text{ V}$	3	6	20	μA
I_{LINh}	\overline{LIN} logic "0" input bias current	$\overline{LIN} = 15\text{ V}$			1	μA
I_{SDh}	\overline{SD} logic "0" input bias current	$\overline{SD} = 15\text{ V}$	30	120	300	μA
I_{SDl}	\overline{SD} logic "1" input bias current	$\overline{SD} = 0\text{ V}$			3	μA
Dt	Dead time	see Figure 5		600		ns

Table 11. Sense comparator characteristics (V_{CC} = 15 V)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I _{ib}	Input bias current	V _{CP+} = 1 V	-		3	μA
V _{ol}	Open-drain low-level output voltage	I _{od} = - 3 mA	-		0.5	V
t _{d_comp}	Comparator delay	\overline{SD}/OD pulled to 5 V through 100 kΩ resistor	-	90	130	ns
SR	Slew rate	C _L = 180 pF; R _{pu} = 5 kΩ	-	60		V/μsec
t _{sd}	Shut down to high / low side driver propagation delay	V _{OUT} = 0, V _{boot} = V _{CC} , V _{IN} = 0 to 3.3 V	50	125	200	ns
t _{isd}	Comparator triggering to high / low side driver turn-off propagation delay	Measured applying a voltage step from 0 V to 3.3 V to pin CIN _i	50	200	250	

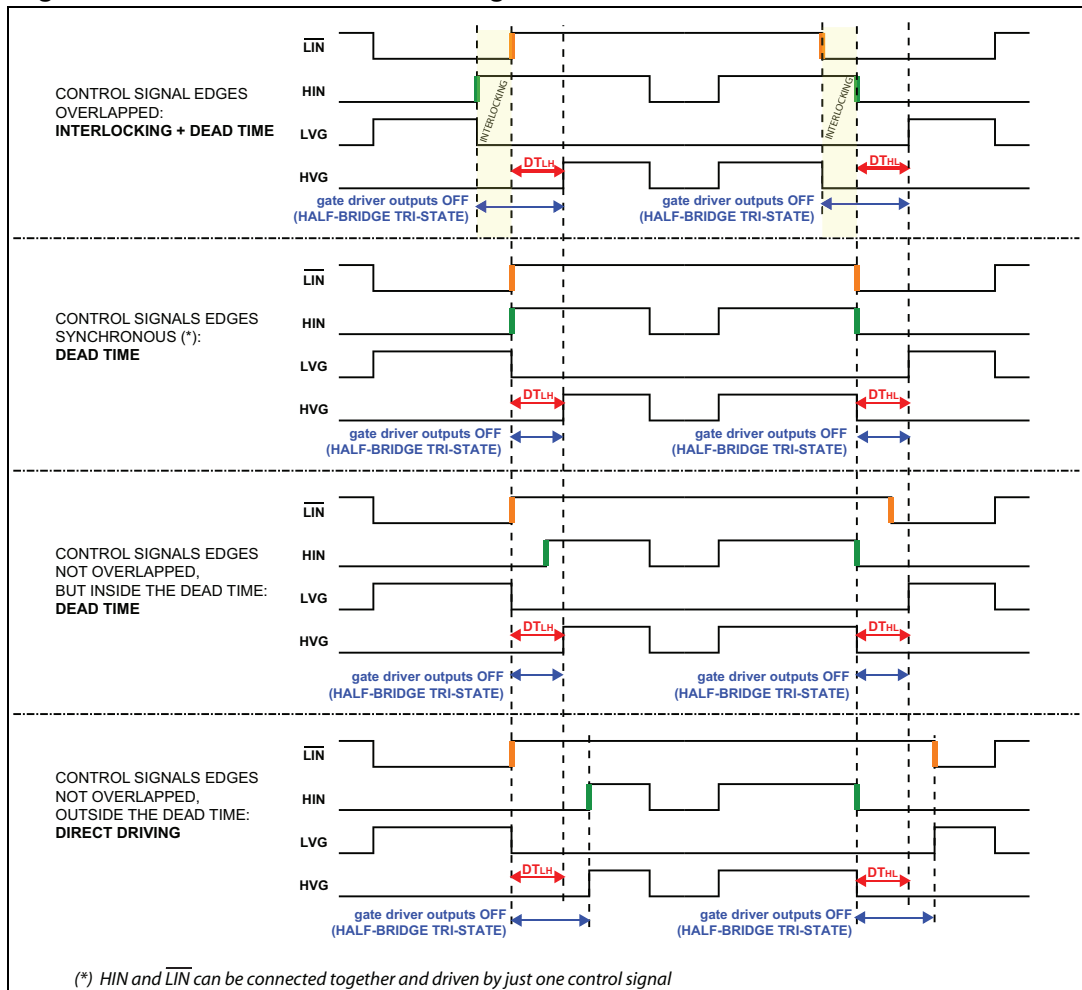
Table 12. Truth table

Condition	Logic input (V _i)			Output	
	\overline{SD}/OD	\overline{LIN}	HIN	LVG	HVG
Shutdown enable half-bridge tri-state	L	X	X	L	L
Interlocking half-bridge tri-state	H	L	H	L	L
0 "logic state" half-bridge tri-state	H	H	L	L	L
1 "logic state" low side direct driving	H	L	L	H	L
1 "logic state" high side direct driving	H	H	H	L	H

Note: X: don't care

3.2 Waveforms definitions

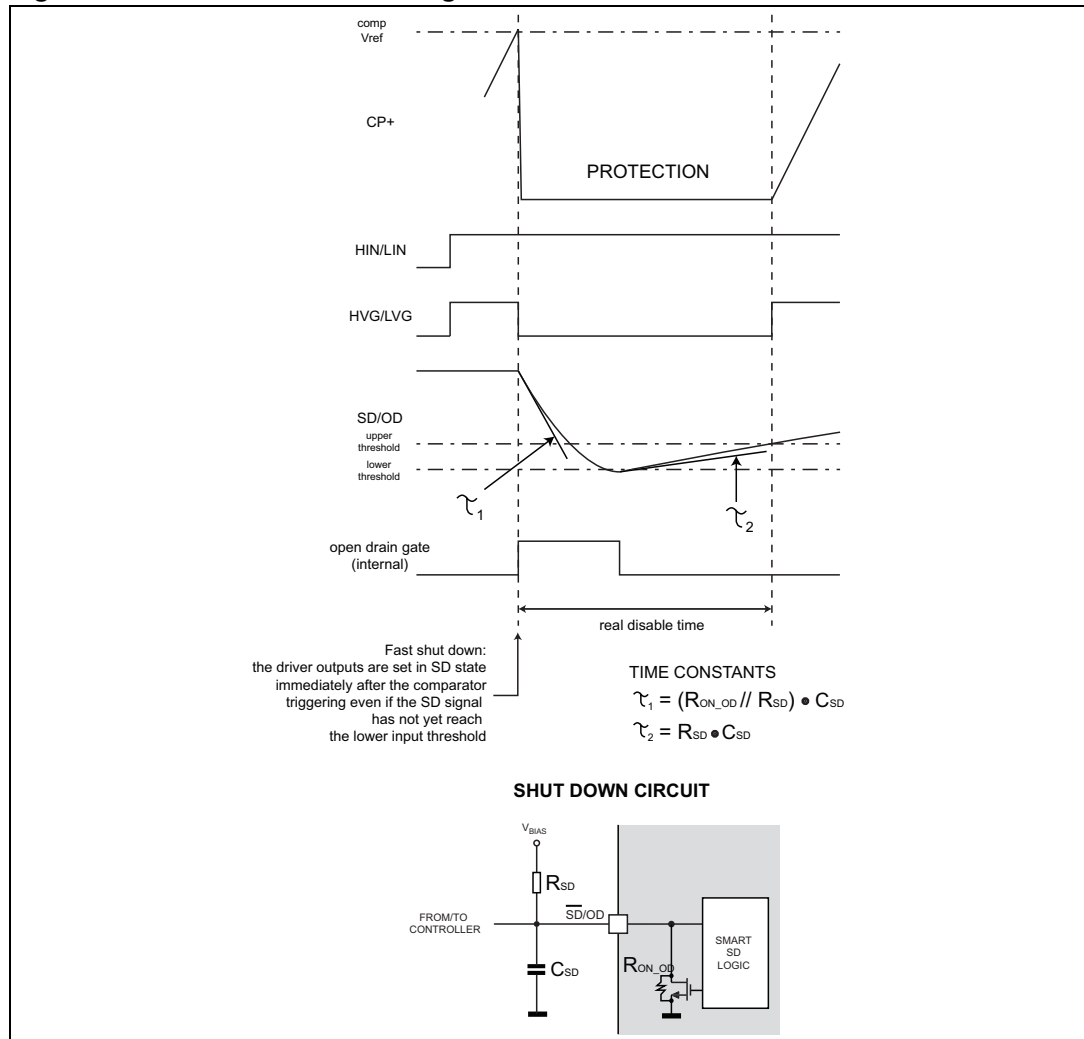
Figure 5. Dead time and interlocking waveforms definitions



4 Smart shutdown function

The STGIPS20K60 integrates a comparator for fault sensing purposes. The comparator non-inverting input (CIN) can be connected to an external shunt resistor in order to implement a simple over-current protection function. When the comparator triggers, the device is set in shutdown state and both its outputs are set to low-level leading the half-bridge in tri-state. In the common overcurrent protection architectures the comparator output is usually connected to the shutdown input through a RC network, in order to provide a mono-stable circuit, which implements a protection time that follows the fault condition. Our smart shutdown architecture allows to immediately turn-off the output gate driver in case of overcurrent, the fault signal has a preferential path which directly switches off the outputs. The time delay between the fault and the outputs turn-off is no more dependent on the RC values of the external network connected to the shutdown pin. At the same time the internal logic turns on the open-drain output and holds it on until the shutdown voltage goes below the logic input lower threshold. Finally the smart shutdown function provides the possibility to increase the real disable time without increasing the constant time of the external RC network.

Figure 6. Smart shutdown timing waveforms



Pls refer to [Table 11](#) for internal propagation delay time details.

5.1 Recommendations

- Input signal HIN is active high logic. A 85 k Ω (typ.) pull down resistor is built-in for each high side input. If an external RC filter is used, for noise immunity, pay attention to the variation of the input signal level.
- Input signal $\overline{\text{LIN}}$ is active low logic. A 720 k Ω (typ.) pull-up resistor, connected to an internal 5 V regulator through a diode, is built-in for each low side input.
- To prevent the input signals oscillation, the wiring of each input should be as short as possible.
- By integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler is possible.
- Each capacitor should be located as nearby the pins of IPM as possible.
- Low inductance shunt resistors should be used for phase leg current sensing.
- Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible. Additional high frequency ceramic capacitor mounted close to the module pins will further improve performance.
- The $\overline{\text{SD}}/\text{OD}$ signal should be pulled up to 5 V / 3.3 V with an external resistor (see [Section 4: Smart shutdown function](#) for detailed info).

Table 13. Recommended operating conditions

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V _{PN}	Supply Voltage	Applied between P-Nu,Nv,Nw		300	400	V
V _{CC}	Control supply voltage	Applied between V _{CC} -GND	13.5	15	18	V
V _{BS}	High side bias voltage	Applied between V _{BOOTi} -OUT _i for i=U,V,W	13		18	V
t _{dead}	Blanking time to prevent Arm-short	For each input signal	1			μs
f _{PWM}	PWM input signal	-40°C < T _c < 100°C -40°C < T _j < 125°C			20	kHz

6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Please refer to dedicated technical note TN0107 for mounting instructions.

Table 14. SDIP-25L package mechanical data

Dim.	(mm.)		
	Min.	Typ.	Max.
A	43.90	44.40	44.90
A1	1.15	1.35	1.55
A2	1.40	1.60	1.80
A3	38.90	39.40	39.90
B	21.50	22.00	22.50
B1	11.25	11.85	12.45
B2	24.70	25.20	25.70
C	5.00	5.40	6.00
C1	6.50	7.00	7.50
C2	11.20	11.70	12.20
e	2.15	2.35	2.55
e1	3.40	3.60	3.80
e2	4.50	4.70	4.90
e3	6.30	6.50	6.70
D		33.30	
D1		5.55	
E		11.20	
E1		1.40	
F	0.85	1.00	1.15
F1	0.35	0.50	0.65
R	1.55	1.75	1.95
T	0.45	0.55	0.65
V	0°		6°

Figure 8. SDIP-25L package dimensions

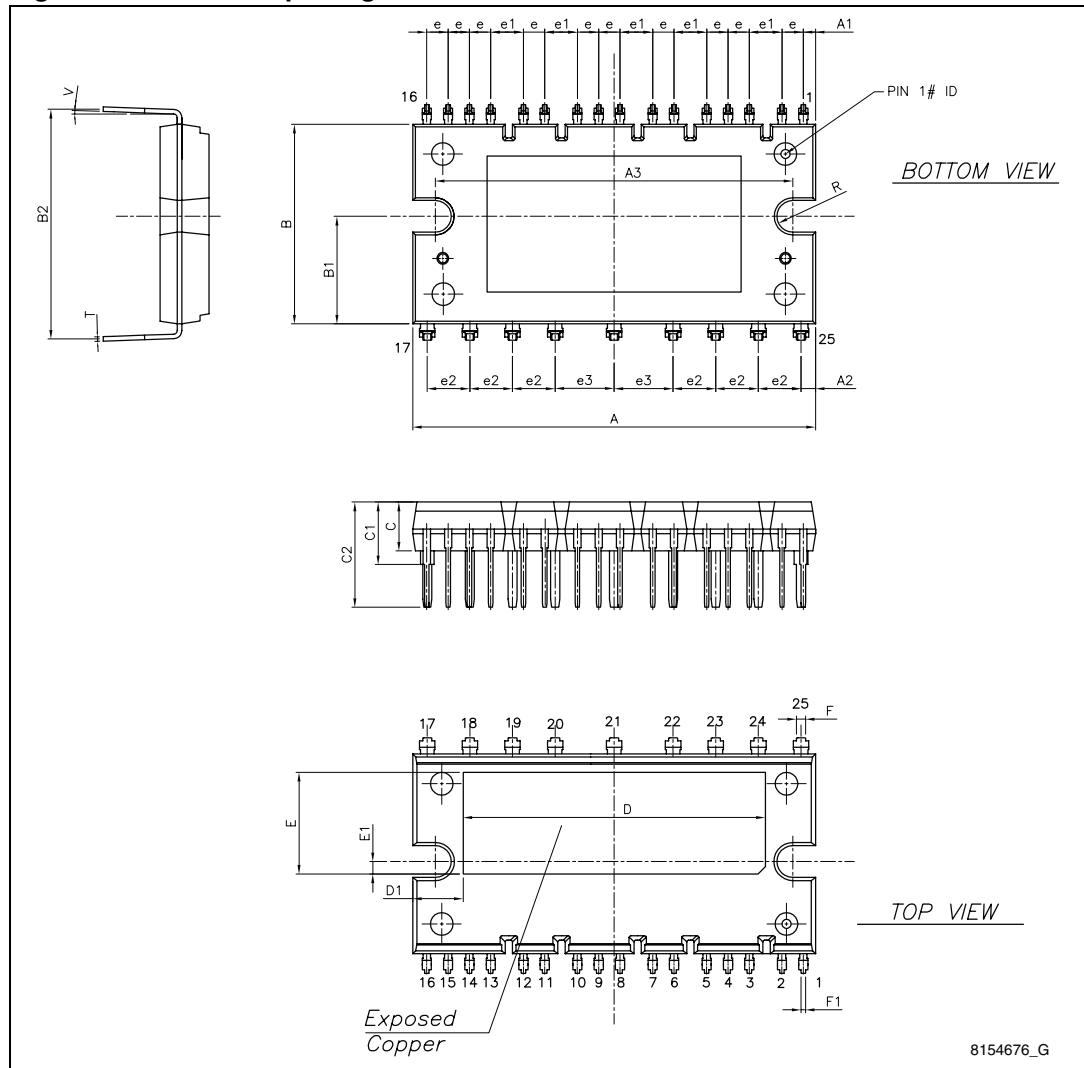
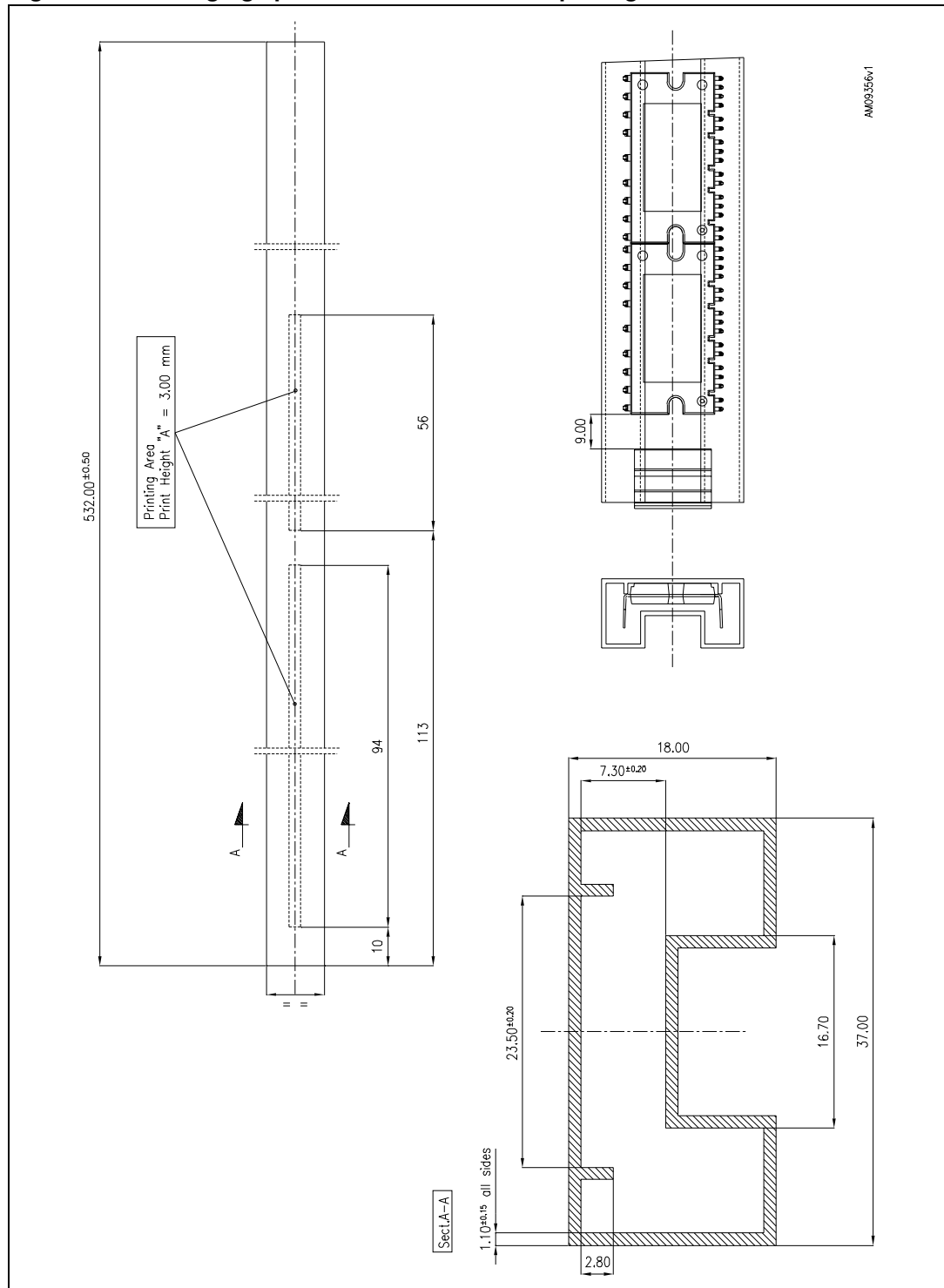


Figure 9. Packaging specifications of SDIP-25L package



7 Revision history

Table 15. Document revision history

Date	Revision	Changes
07-Dec-2011	1	Initial release

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